

M5210L, P, FP

DUAL HIGH-VOLTAGE, HIGH S/N OPERATIONAL AMPLIFIERS (DUAL POWER SUPPLY TYPE)

DESCRIPTION

The M5210 is a semiconductor integrated circuit designed for a preamplifier in audio equipment of stereo and cassette tape decks.

Two low-noise operational amplifier circuits displaying internal phase-compensated high gain and low distortion are contained in a 8-pin (SIP, DIP), suitable for application as a microphone and tone control amplifier of stereo equipment and cassette tape decks.

The unit can also be used as a general-purpose amplifier in portable equipment such as a stereo cassette tape recorder of a single power supply type as it operates at a low supply voltage.

FEATURES

- Low noise $V_{NI}=1.0\mu V_{rms}$ typ. ($R_g=2.2k\Omega$, FLAT)
 $S/N=66dB$ typ. ($R_g=600\Omega$, IHF-A network)
(microphone amplifier, reference input = $-60dBm$)
Higher S/N ratio by 10dB when compared to ordinary operational amplifiers
 - High voltage $V_{CC}=\pm 25V(50V)$
 - Low maximum input voltage $V_i=140mV_{rms}$ (typ.)
 $(V_{CC}=\pm 22.5V, G_V=40dB)$
 - High gain, low distortion $G_{VO}=113dB, THD=0.002\%$ (typ.)
 - High slew rate $SR=6.5V/\mu s$ (typ.)
 - High load current, high power dissipation $I_{LP}=\pm 50mA, P_d=800mW(SIP)$
 $P_d=625mW(DIP), P_d=440mW(FP)$

APPLICATION

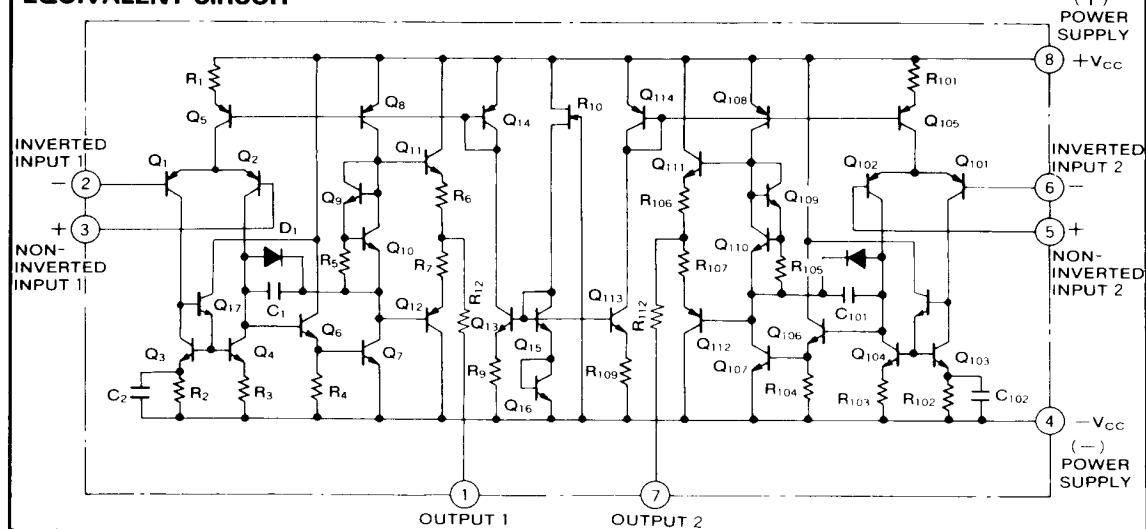
General-purpose preamplifier in stereo equipment, tape decks and radio stereo cassette recorders

RECOMMENDED OPERATING CONDITIONS

Supply voltage range $\pm 2 \sim \pm 22.5$ V

Rated supply voltage ±22.5V

EQUIVALENT CIRCUIT



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ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$, unless otherwise noted)

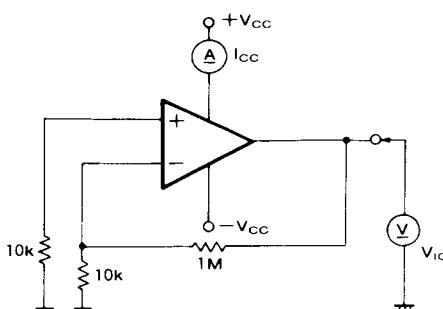
Symbol	Parameter	Conditions	Ratings	Unit
V_{CC}	Supply voltage		$\pm 25(50)$	V
I_{LP}	Load current		± 50	mA
V_{id}	Differential input voltage		± 30	V
V_{ic}	Common input voltage		± 22.5	V
P_d	Power dissipation		800(SIP)/625(DIP)/440(FP)	mW
K_θ	Thermal derating	$T_a \geq 25^\circ\text{C}$	8(SIP)/6.25(DIP)/4.4(FP)	mW/°C
T_{opr}	Operating temperature		$-20 \sim +75$	°C
T_{stg}	Storage temperature		$-55 \sim +125$	°C

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$, $V_{CC}=\pm 22.5\text{V}$)

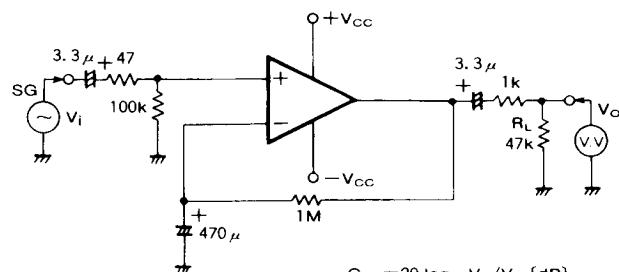
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
I_{CC}	Circuit current	$V_{in}=0$	2.0	4.0	8.0	mA
V_{IO}	Input offset voltage	$R_s \leq 10\text{k}\Omega$		0.5	6.0	mV
I_B	Input bias current			0.7		μA
G_{VO}	Open loop voltage gain	$f=100\text{Hz}, R_L=47\text{k}\Omega, C_{NF}=470\mu\text{F}$	90	113		dB
V_{OM}	Maximum output voltage	$f=1\text{kHz}, THD=0.1\%, R_L=47\text{k}\Omega, \text{FLAT}$	12.5	14.2		Vrms
THD	Total harmonic distortion	$f=1\text{kHz}, V_O=10\text{Vrms}, R_L=47\text{k}\Omega, \text{FLAT}$		0.002		%
V_{NI}	Input-referred noise voltage	$R_g=2.2\text{k}\Omega, BW=10\text{Hz} \sim 30\text{kHz}, \text{FLAT}$		1.0	1.5	μVrms
S/N	Signal to noise ratio	$R_g=600\Omega, G_V=40\text{dB}, \text{IHF-A network}$ Reference input -60dBm (microphone)		66		dB

TEST CIRCUITS

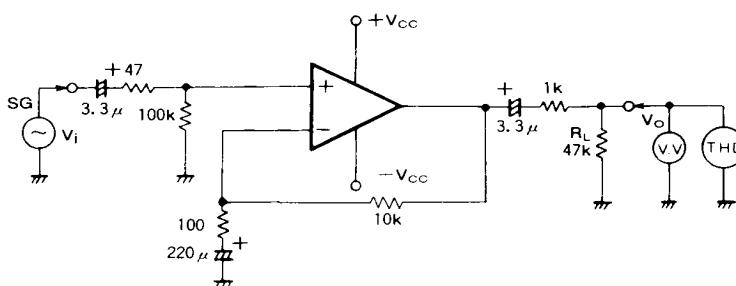
(a) I_{CC}, V_{IO}



(b) G_{VO}



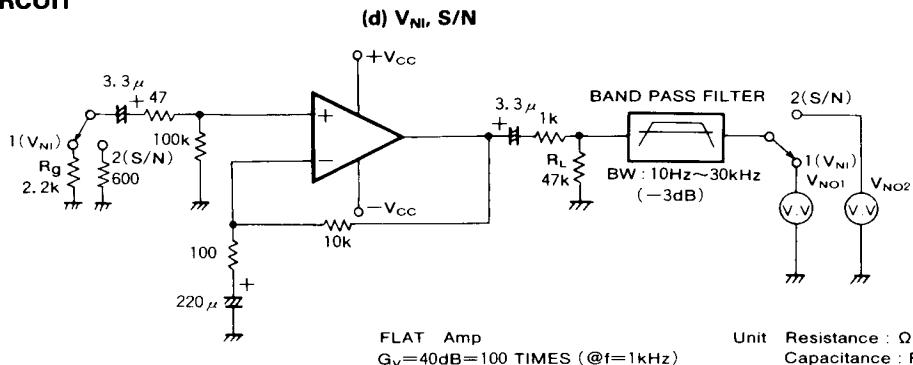
(c) V_{OM}, THD



Unit Resistance : Ω
Capacitance : F

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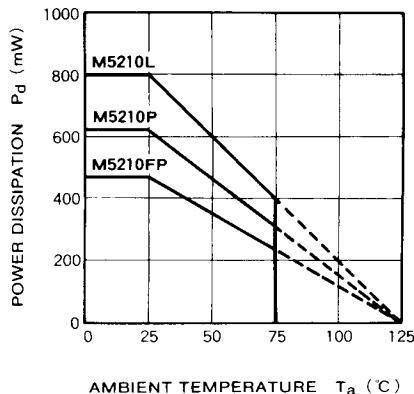
TEST CIRCUIT



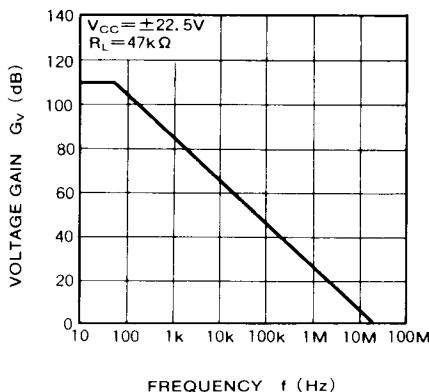
1. $V_{NI} = V_{NO1}/100(\mu\text{Vrms})$
 2. $S/N = 20 \log [775\mu\text{Vrms}/(V_{NO2}/100)] \text{ (dB)}$ $775\mu\text{Vrms} = -60\text{dBm}$ (microphone reference input voltage)
- * An AC voltmeter V.V with a built-in HF-A network filter should be used for measuring the S/N ratio.

TYPICAL CHARACTERISTICS

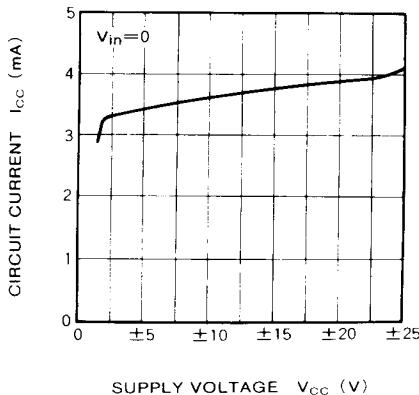
**THERMAL DERATING
(MAXIMUM RATING)**



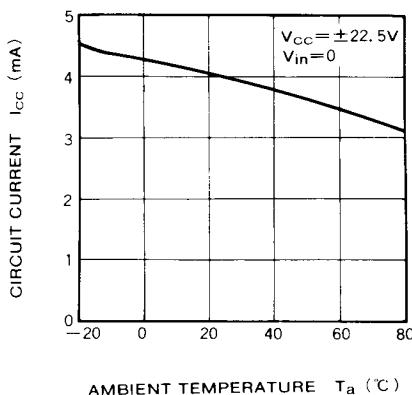
**VOLTAGE GAIN VS.
FREQUENCY RESPONSE**



**CIRCUIT CURRENT VS.
SUPPLY VOLTAGE**



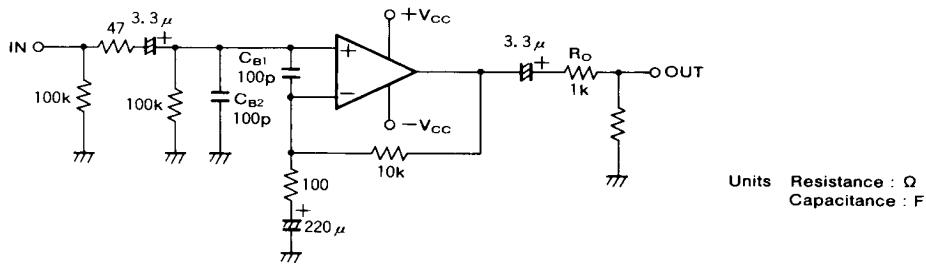
**CIRCUIT CURRENT VS.
AMBIENT TEMPERATURE**



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APPLICATION EXAMPLES

(1) Stereo FLAT (microphone) amplifier circuit



TYPICAL CHARACTERISTICS ($V_{CC} = \pm 22.5V$, FLAT)

- $G_V = 40\text{dB}$ ($f = 1\text{kHz}$)
- $V_{NI} = 1.0\text{ }\mu\text{VRms}$ ($R_g = 2.2\text{k}\Omega$, $BW = 10\text{Hz} \sim 30\text{kHz}$)
- $S/N = 66\text{dB}$ (IHF-A network, $R_g = 600\Omega$, -60dBm input sensitivity)
- THD = 0.002% ($f = 1\text{kHz}$, $V_o = 10\text{Vrms}$)

Left channel circuit constants are identical to those of right channel

C_{B1}, C_{B2} : Capacitors for buzz prevention, use if required.

R_O : Resistor used to prevent parasitic oscillation for capacitive loads and current limiting with shorted and other abnormal load conditions.

